## Layer-dependent Optical Conductivity of MBE-grown ZrTe<sub>2</sub>

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Besides providing an interesting platform to interrogate fundamental physics questions, twodimensional transition metal dichalcogenides (TMDCs) are well suited to advance the development of optoelectronic technologies. In this work, we investigated the growth and the optical properties of ZrTe<sub>2</sub>, a candidate topological Dirac semimetal, grown using molecular beam epitaxy. During the growth of 12 unit cells (u.c.) of ZrTe<sub>2</sub> on a sapphire substrate, we obtained in-situ spectroscopic ellipsometry after the deposition of each u.c. Additionally, we obtained temperature dependent ellipsometry data on the sample between 20 °C and 350 °C. After the deposition of the ZrTe<sub>2</sub> layers, a Te capping layer was deposited in order to protect the TMDC film. Post-growth X-ray reflectivity measurements indicated that the total thickness of ZrTe<sub>2</sub> and the thickness of Te to be 5.95 nm and 19 nm, respectively.

A standard inversion technique was used to model the ellipsometry spectra by specifying a three layer model (i.e., sapphire substrate. ZrTe<sub>2</sub> layer and the Te capping layer) to fit the final ellipsometry spectra. The thicknesses obtained from X-ray reflectivity allowed us to obtain the precise dielectric function of the final ZrTe<sub>2</sub> layer (i.e., 12 u.c.), which was converted to the



Fig. 1. Total conductivity (black-lines) and contributions from free electrons (green-lines) and band electrons (red and blue lines) for different thicknesses of ZrTe<sub>2</sub>.

optical conductivity. Subsequently, we fit the remaining ellipsometry spectra obtained for 11 u.c. through 1 u.c.  $ZrTe_2$  layers. Clearly, the optical conductivity shows a noticeable change with the thickness of the  $ZrTe_2$  layers, where the real part increases with the thickness of  $ZrTe_2$ , as shown in Fig. 1. The layer-dependent conductivity was further analyzed by incorporating a Drude oscillator to account for free electrons, and two Kramers-Kronig-consistent oscillators to represent the band-to-band transitions. Interestingly, we find that the Drude contribution reduces as the thickness of  $ZrTe_2$  gets smaller, suggesting that its metallic character diminishes as the thickness reduces.